

# InGaAs PIN photodiode arrays



G12430 series

## 16/32/46 element InGaAs array for near IR detection

The G12430 series is one-dimensional InGaAs PIN photodiode array in a ceramic DIP (dual inline package). It can be used to perform simple spectroscopic analysis.

### Features

- 16, 32, or 46 element array
- Designed for simple measurement
- Large photosensitive area size

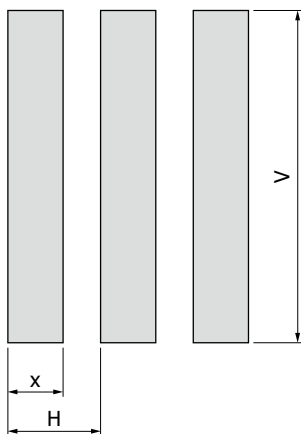
### Applications

- NIR spectrophotometers

### Structure

Parameter	G12430-016D	G12430-032D	G12430-046D	Unit
Cooling	Room temperature type			-
Number of elements	16	32	46	elements
Elements size	0.45 × 1	0.2 × 1		mm
Element pitch	0.5	0.25		mm
Package	18-pin ceramic DIP	40-pin ceramic DIP	48-pin ceramic DIP	-
Window material	Borosilicate glass			-

### Details of photosensitive area



Number of elements	x	H	V	Unit
16	0.45	0.5	1	mm
32	0.2	0.25		
46				

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Static electricity can damage or degrade the G12430 series. Use caution when handling.

### Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Reverse voltage	V <sub>R</sub> max.	5	V
Operating temperature	T <sub>opr</sub>	-20 to +70*	°C
Storage temperature	T <sub>stg</sub>	-20 to +85*	°C
Soldering conditions	-	260 °C or less, within 5 s	-

\* No dew condensation

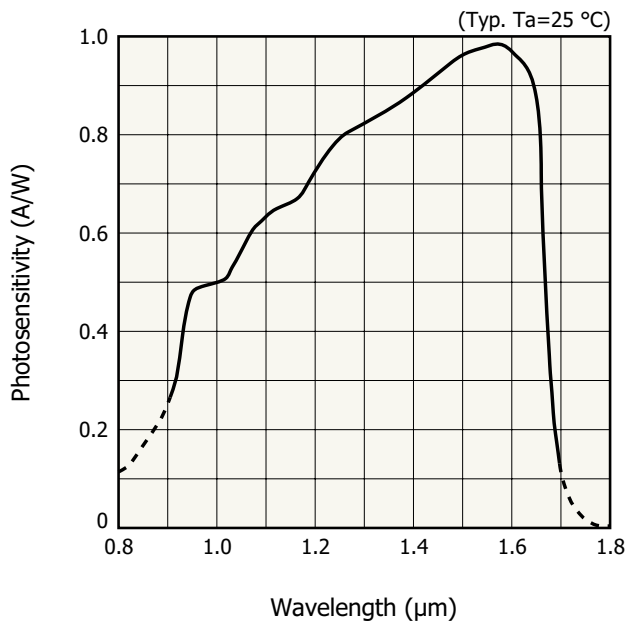
When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

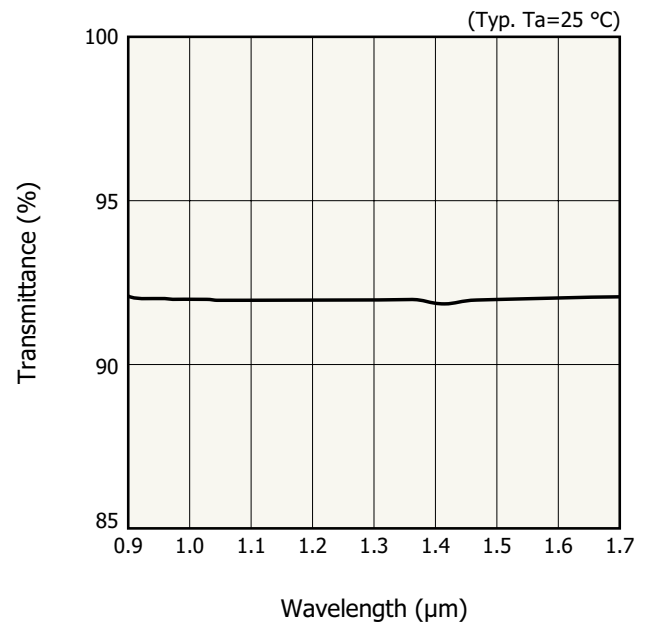
### Electrical and optical characteristics (Ta=25 °C, per element)

Parameter	Symbol	Condition	G12430-016D			G12430-032D			G12430-046D			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	$\lambda$		-	0.9 to 1.7	-	-	0.9 to 1.7	-	-	0.9 to 1.7	-	$\mu\text{m}$
Peak sensitivity wavelength	$\lambda_p$		-	1.55	-	-	1.55	-	-	1.55	-	$\mu\text{m}$
Photosensitivity	S	$\lambda = \lambda_p$	0.85	0.95	-	0.85	0.95	-	0.85	0.95	-	A/W
Dark current	I <sub>D</sub>	V <sub>R</sub> =1 V	-	500	2500	-	250	1250	-	250	1250	pA
Dark current temperature coefficient	$\Delta T_{ID}$	V <sub>R</sub> =10 mV	-	1.1	-	-	1.1	-	-	1.1	-	times/°C
Cutoff frequency	f <sub>c</sub>	V <sub>R</sub> =1 V, R <sub>L</sub> =50 $\Omega$ $\lambda = 1.3 \mu\text{m}$ , -3 dB	15	30	-	25	60	-	25	60	-	MHz
Terminal capacitance	C <sub>t</sub>	V <sub>R</sub> =1 V, f=1 MHz	-	60	100	-	35	60	-	35	60	pF
Shunt resistance	R <sub>sh</sub>	V <sub>R</sub> =10 mV	20	100	-	40	200	-	40	200	-	M $\Omega$
Detectivity	D*	$\lambda = \lambda_p$	$1 \times 10^{12}$	$5 \times 10^{12}$	-	$1 \times 10^{12}$	$5 \times 10^{12}$	-	$1 \times 10^{12}$	$5 \times 10^{12}$	-	cm·Hz <sup>1/2</sup> /W
Noise equivalent power	NEP	$\lambda = \lambda_p$	-	$2 \times 10^{-14}$	$4 \times 10^{-14}$	-	$1 \times 10^{-14}$	$3 \times 10^{-14}$	-	$1 \times 10^{-14}$	$3 \times 10^{-14}$	W/Hz <sup>1/2</sup>

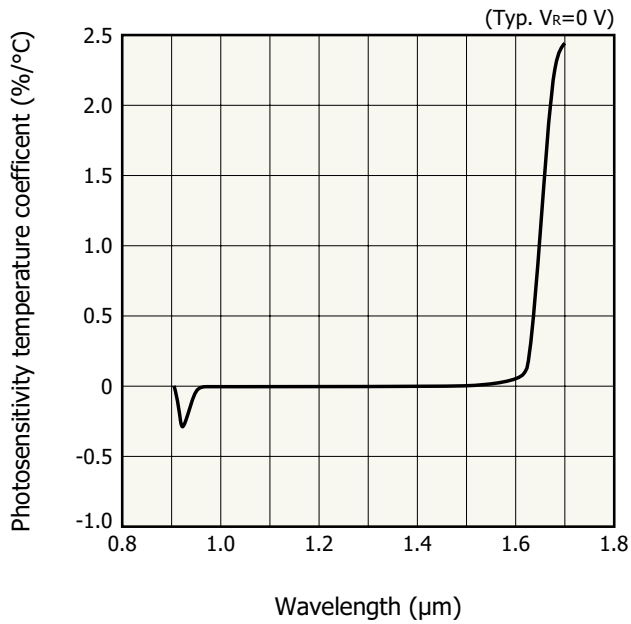
### Spectral response



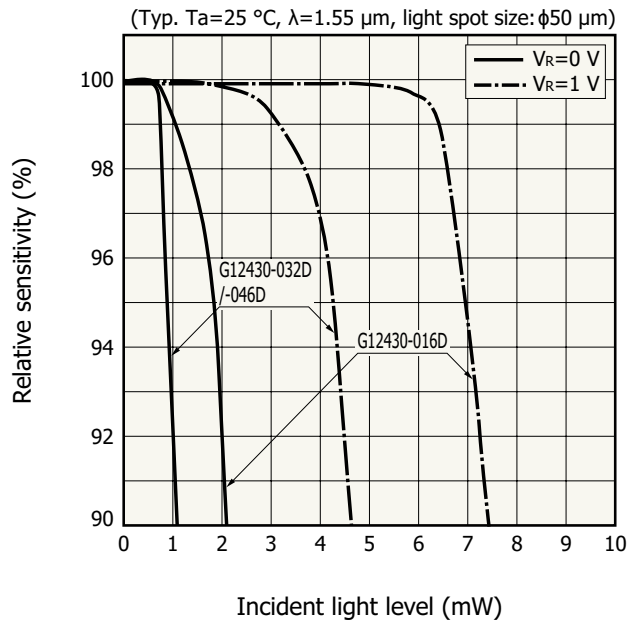
### Spectral transmittance of window material



Photosensitivity temperature characteristics

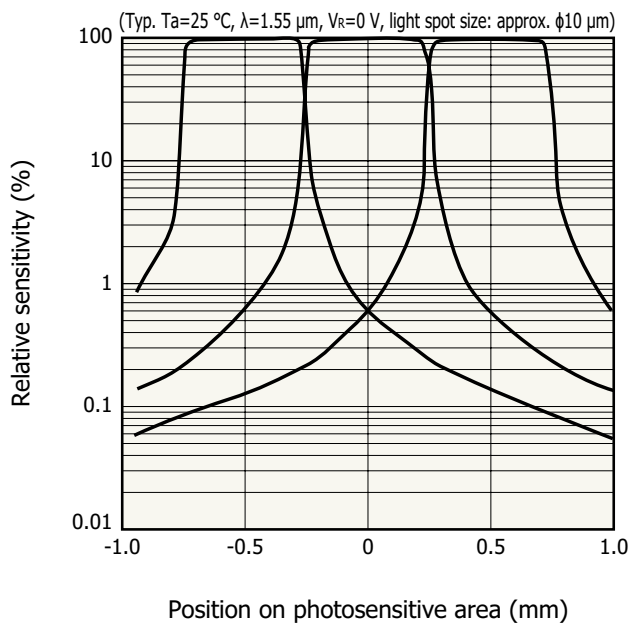


Linearity

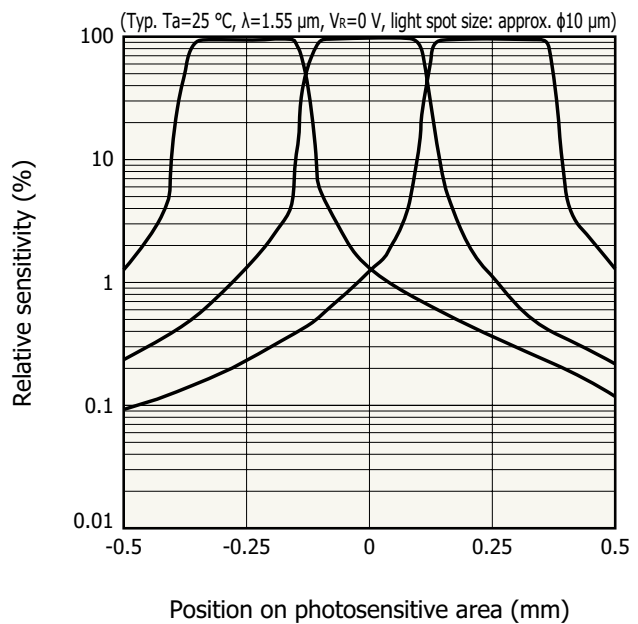


Cross-talk characteristics

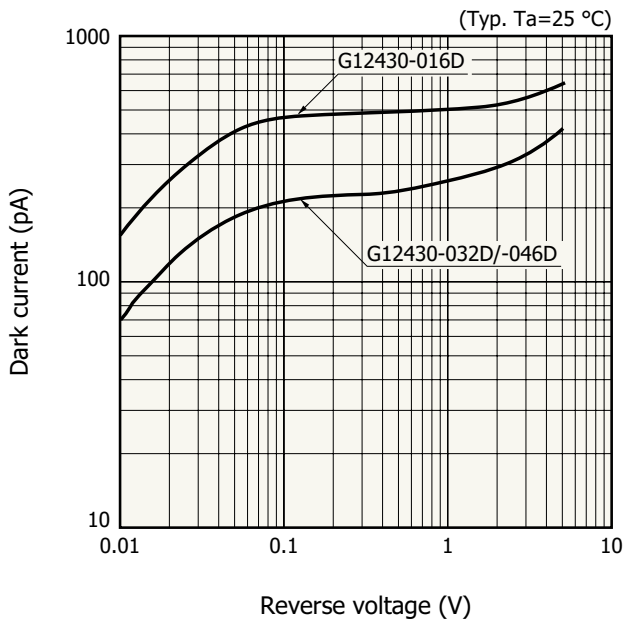
G12430-016D



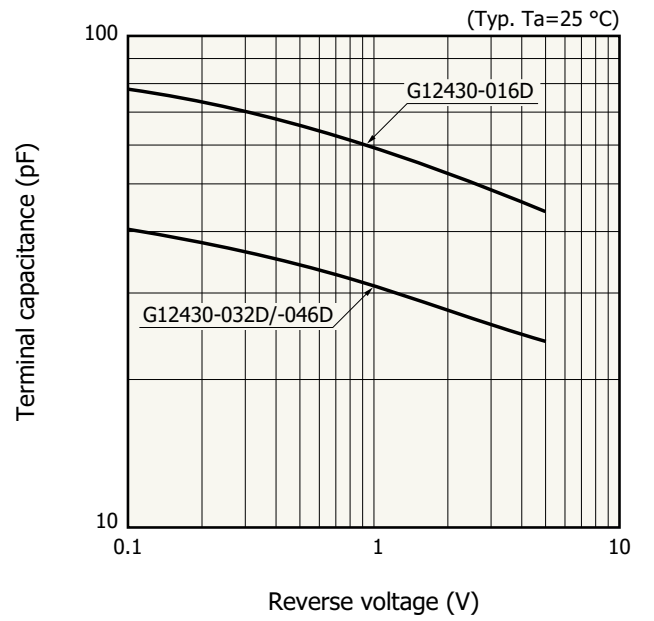
G12430-032D/-046D



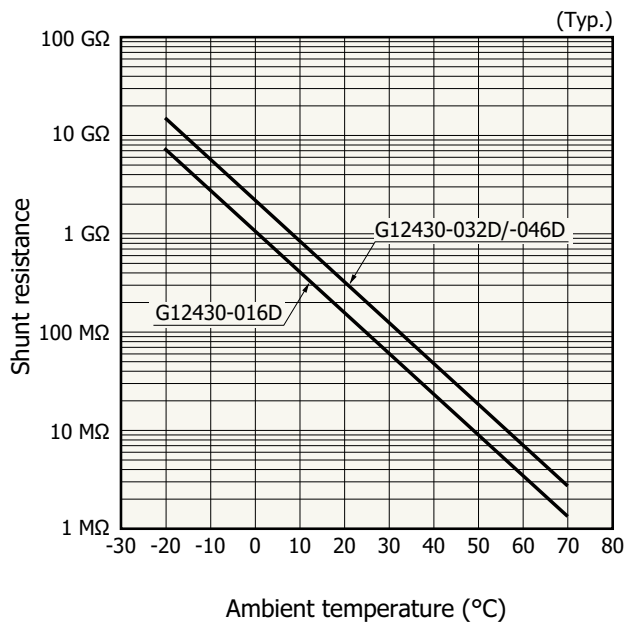
**Dark current vs. reverse voltage**



**Terminal capacitance vs. reverse voltage**

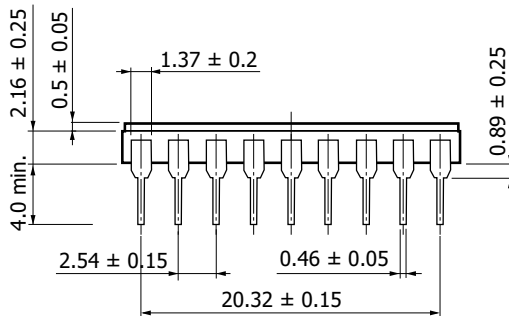
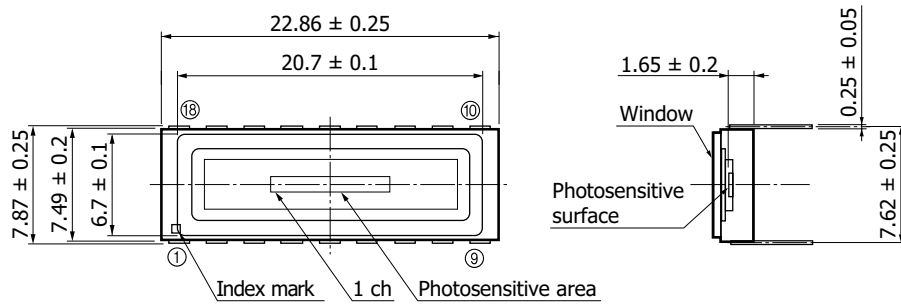


**Shunt resistance vs. ambient temperature**



Dimensional outlines (unit: mm)

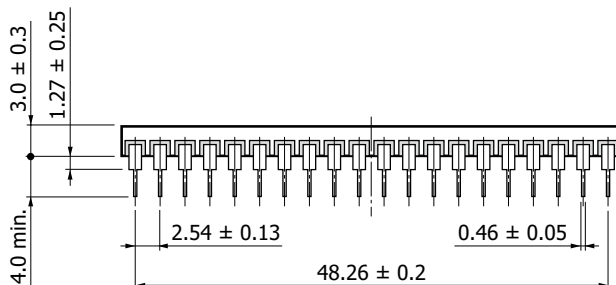
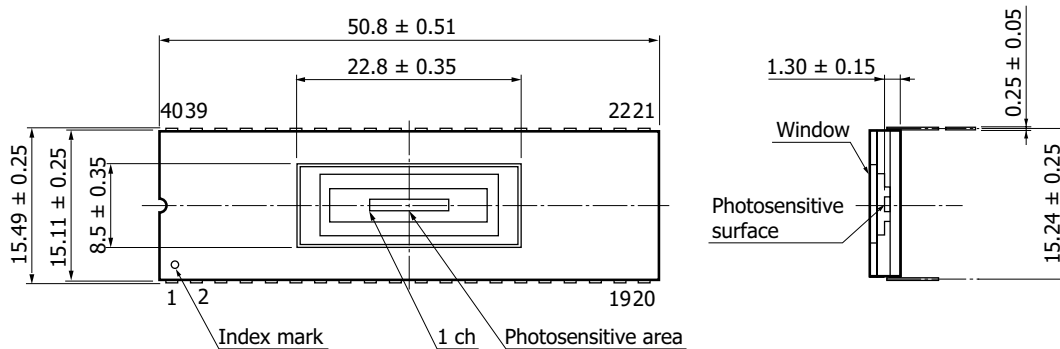
G12430-016D



Package material: Ceramic  
 Lead treatment: Ni/Au plating  
 Lead material: FeNi alloy  
 Reflective index of window material: 1.47  
 Window thickness:  $0.5 \pm 0.05$   
 AR coat: None  
 Window sealing method: Resin sealing  
 Position accuracy of photosensitive area center:  
 $-0.3 \leq X \leq +0.3$   
 $-0.3 \leq Y \leq +0.3$   
 Position accuracy of photosensitive area inclination:  
 $-5^\circ \leq \theta \leq +5^\circ$

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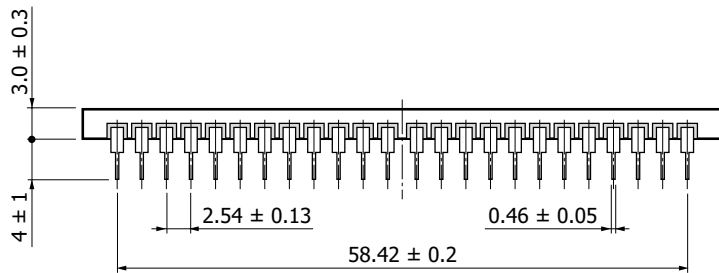
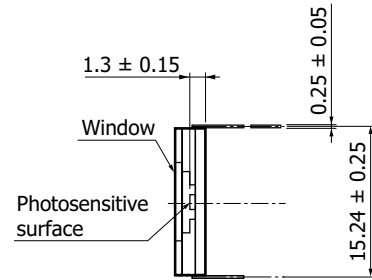
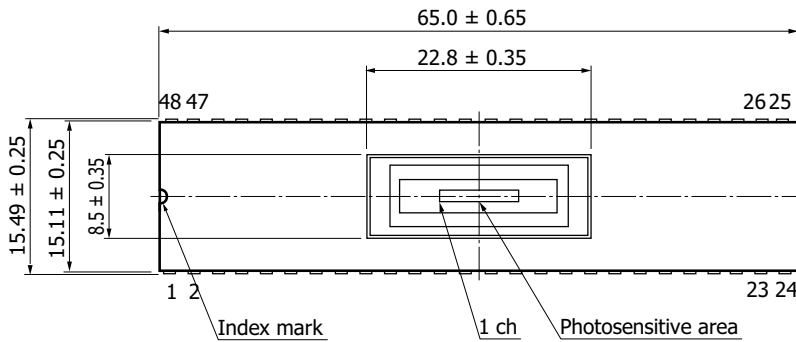
G12430-032D



Package material: Ceramic  
 Lead treatment: Ni/Au plating  
 Lead material: FeNi alloy  
 Reflective index of window material: 1.47  
 Window thickness:  $0.75 \pm 0.05$   
 AR coat: None  
 Window sealing method: Resin sealing  
 Position accuracy of photosensitive area center:  
 $-0.3 \leq X \leq +0.3$   
 $-0.3 \leq Y \leq +0.3$   
 Position accuracy of photosensitive area inclination:  
 $-5^\circ \leq \theta \leq +5^\circ$

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G12430-046D



Package material: Ceramic  
 Lead treatment: Ni/Au plating  
 Lead material: FeNi alloy  
 Reflective index of window material: 1.47  
 Window thickness:  $0.75 \pm 0.05$   
 AR coat: None  
 Window sealing method: Resin sealing  
 Position accuracy of photosensitive area center:  
 $-0.3 \leq X \leq +0.3$   
 $-0.3 \leq Y \leq +0.3$   
 Position accuracy of photosensitive area inclination:  
 $-5^\circ \leq \theta \leq +5^\circ$

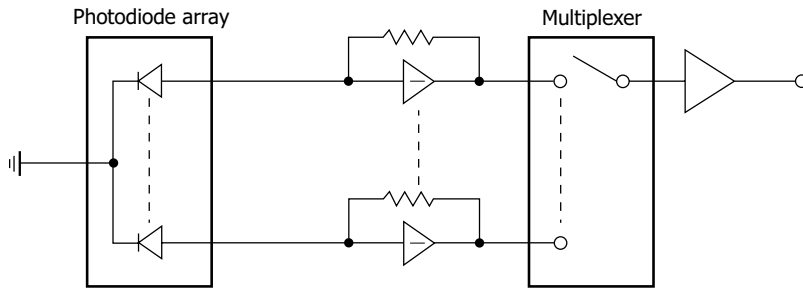
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**Pin connections**

Pin no.	G12430-016D	G12430-032D	G12430-046D	Pin no.	G12430-016D	G12430-032D	G12430-046D
1	KC	KC	KC	25	-	27	KC
2	2	NC	2	26	-	25	45
3	4	2	4	27	-	23	43
4	6	4	6	28	-	21	41
5	8	6	8	29	-	19	39
6	10	8	10	30	-	17	37
7	12	10	12	31	-	15	35
8	14	12	14	32	-	13	33
9	16	14	16	33	-	11	31
10	KC	16	18	34	-	9	29
11	15	18	20	35	-	7	27
12	13	20	22	36	-	5	25
13	11	22	24	37	-	3	23
14	9	24	26	38	-	1	21
15	7	26	28	39	-	NC	19
16	5	28	30	40	-	NC	17
17	3	30	32	41	-	-	15
18	1	32	34	42	-	-	13
19	-	NC	36	43	-	-	11
20	-	NC	38	44	-	-	9
21	-	KC	40	45	-	-	7
22	-	NC	42	46	-	-	5
23	-	31	44	47	-	-	3
24	-	29	46	48	-	-	1

## Operating circuit

In the most generally used circuit, op amplifiers are connected to each channel to read the output in real time. The output of an op amplifier is of low impedance and thus can be easily multiplexed.



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## Related information

[www.hamamatsu.com/sp/ssd/doc\\_en.html](http://www.hamamatsu.com/sp/ssd/doc_en.html)

### ■ Precautions

- Disclaimer
- Safety consideration
- Compound opto-semiconductors (photodensors, light emitters)

### ■ Technical note

- Compound semiconductor photosensors

Information described in this material is current as of April 2024.

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